

Status of CNM developments on LGAD and iLGAD detectors

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We will present the last technological developments at CNM on LGAD and iLGAD detectors. The last electrical performances for pad and strip LGADs will also be presented, showing that the fabricated LGAD detectors have a voltage capability higher than 1000 V with leakage currents in the 20 nA/cm² range, and a linear gain in the typical operating reverse voltage values (200 to 800 V) in the range of 5-10. However, red laser scanning measurements revealed a non-uniform multiplication across the strip LGAD, basically due to technological constrains.

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